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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Filed: November 29, 2007

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Sheet 1 of 3

Complete if Known

Application Number	Unassigned 10590485
Filing Date	04/02/08
First Named Inventor	Igor BARGATIN et al.
Group Art Unit	Unassigned 2855
Examiner Name	Unassigned M. Noori
Attorney Docket Number	049411-0340

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
/MN/	A1	2002/0166962	A1	ROUKES et al.	11/14/2002	
	A2	2002/0175408	A1	MAJUMDAR et al.	11/28/2002	
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/MN/	A30	WO	2003/095616	A2	California Inst. of Tech.	11/20/2003		
/MN/	A31	WO	2003/095617	A2	California Inst. of Tech.	11/20/2003		
/MN/	A32	WO	2004/041998	A2	California Inst. of Tech.	05/21/2004		

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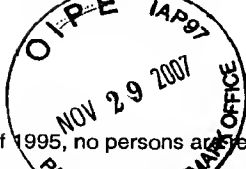
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT Filed: <u>November 29, 2007</u> (use as many sheets as necessary)		Application Number	<u>Unassigned 10590485</u>
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		First Named Inventor	<u>Igor BARGATIN et al.</u>
		Group Art Unit	<u>Unassigned 2855</u>
		Examiner Name	<u>Unassigned M. Noori</u>
Sheet	<u>2</u>	of	<u>3</u>
		Attorney Docket Number	<u>049411-0340</u>

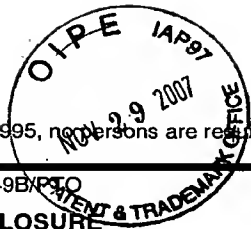
NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
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Examiner Signature	<u>/Max Noori/</u>	Date Considered	<u>10/30/2008</u>
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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Sheet 3 of 3

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Examiner Name	Unassigned M. Noori
Attorney Docket Number	049411-0340

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
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